FEATURES

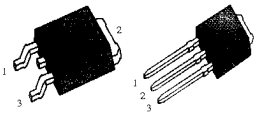
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- 175°C Operating Temperature
- Lower Leakage Current: 10μA (Max.) @ V_{DS} = 60V
- Lower $R_{DS(ON)}$: 0.050Ω (Typ.)

BV_{DSS} = 60 V

$R_{DS(on)}$ = 0.07Ω

I_D = 17 A

D^2-PAK I^2-PAK



1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current (T_C=25°C)	17	A
	Continuous Drain Current (T_C=100°C)	12	
I_{DM}	Drain Current-Pulsed (1)	68	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy (2)	149	mJ
I_{AR}	Avalanche Current (1)	17	A
E_{AR}	Repetitive Avalanche Energy (1)	4.4	mJ
dv/dt	Peak Diode Recovery dv/dt (3)	5.5	V/ns
P_D	Total Power Dissipation (T_A=25°C) *	3.8	W
	Total Power Dissipation (T_C=25°C)	44	W
	Linear Derating Factor	0.29	W/°C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +175	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8. from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	3.43	°C/W
$R_{\theta JA}$	Junction-to-Ambient *	--	40	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

* When mounted on the minimum pad size recommended (PCB Mount).

Rev. B

FAIRCHILD SEMICONDUCTOR™

Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	60	--	--	V	V_{GS}=0V,I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.064	--	V/°C	I_D=250μA See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=5V,I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=20V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-20V
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	V_{DS}=60V
		--	--	100		V_{DS}=48V,T_C=150°C
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.07	Ω	V_{GS}=10V,I_D=8.5A (4)
g_{fs}	Forward Transconductance	--	10.8	--	Ω	V_{DS}=30V,I_D=8.5A (4)
C_{iss}	Input Capacitance	--	600	780	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz See Fig 5
C_{oss}	Output Capacitance	--	210	240		
C_{rss}	Reverse Transfer Capacitance	--	83	95		
$t_{d(on)}$	Turn-On Delay Time	--	13	30	ns	V_{DD}=30V,I_D=17A, R_G=18Ω See Fig 13 (4) (5)
t_r	Rise Time	--	19	40		
$t_{d(off)}$	Turn-Off Delay Time	--	46	100		
t_f	Fall Time	--	48	100		
Q_g	Total Gate Charge	--	24	32	nC	V_{DS}=48V,V_{GS}=10V, I_D=17A See Fig 6 & Fig 12 (4) (5)
Q_{gs}	Gate-Source Charge	--	4.3	--		
Q_{gd}	Gate-Drain (. Miller.) Charge	--	10.8	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	17	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current (1)	--	--	68		
V_{SD}	Diode Forward Voltage (4)	--	--	1.5	V	T_J=25°C,I_S=17A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	60	--	ns	T_J=25°C,I_F=17A
Q_{rr}	Reverse Recovery Charge	--	0.12	--	μC	di_F/dt=100A/μs (4)

Notes;
(1) Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
(2) L=0.6mH, I_{AS}=17A, V_{DD}=25V, R_G=27Ω, Starting T_J=25°C
(3) I_{SD} ≤ 17A, di/dt ≤ 250A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C
(4) Pulse Test: Pulse Width = 250μs, Duty Cycle ≤ 2%
(5) Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

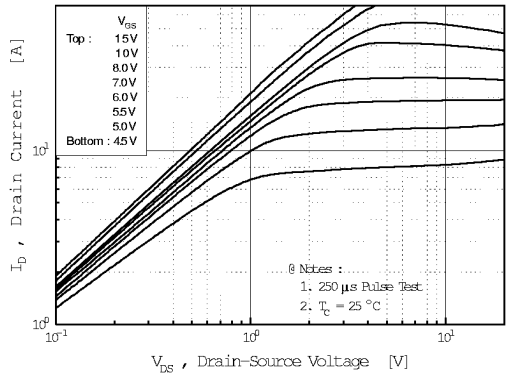


Fig 2. Transfer Characteristics

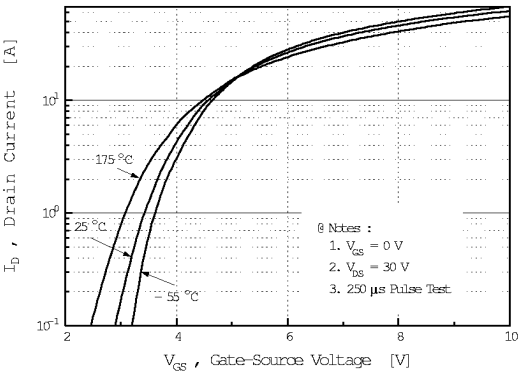


Fig 3. On-Resistance vs . Drain Current

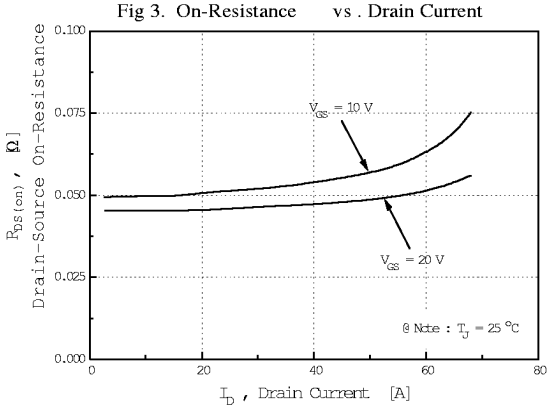


Fig 4. Source-Drain Diode Forward Voltage

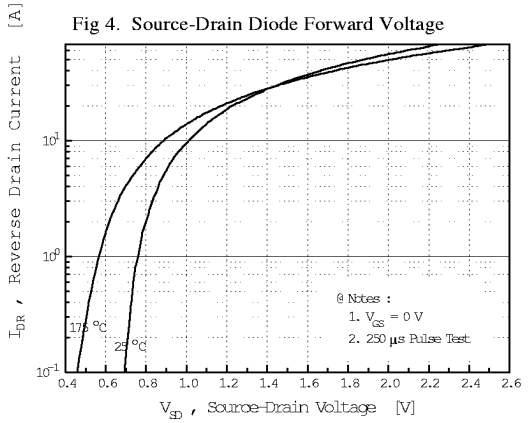


Fig 5. Capacitance vs . Drain-Source Voltage

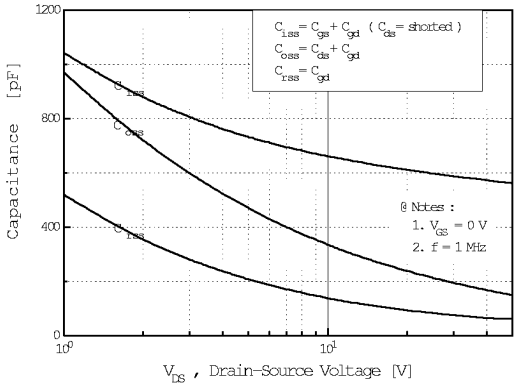


Fig 6. Gate Charge vs . Gate-Source Voltage

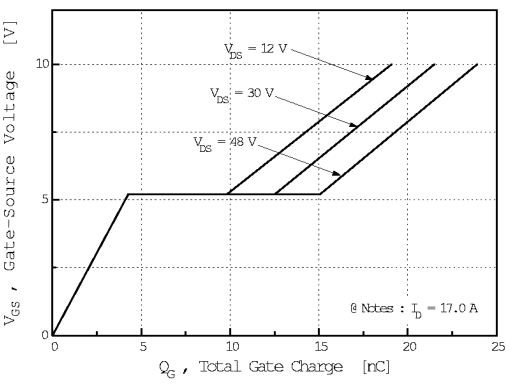


Fig 7. Breakdown Voltage vs . Temperature

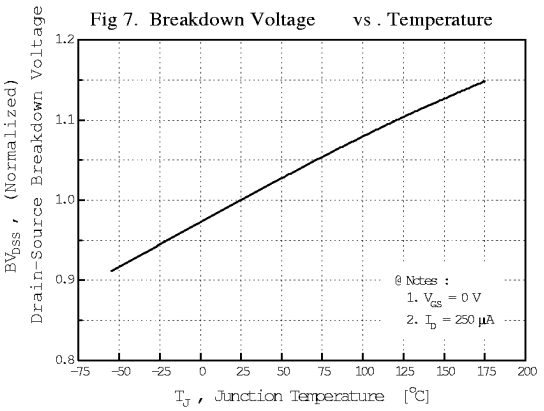


Fig 8. On-Resistance vs . Temperature

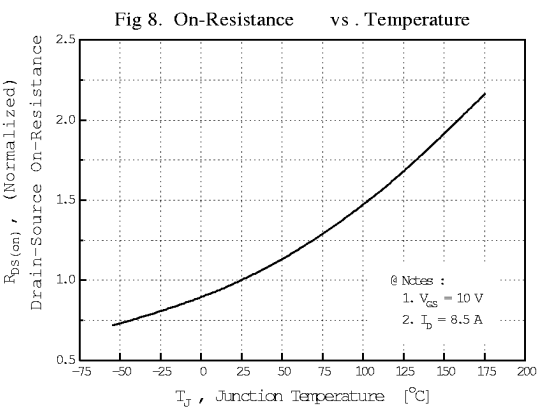


Fig 9. Max. Safe Operating Area

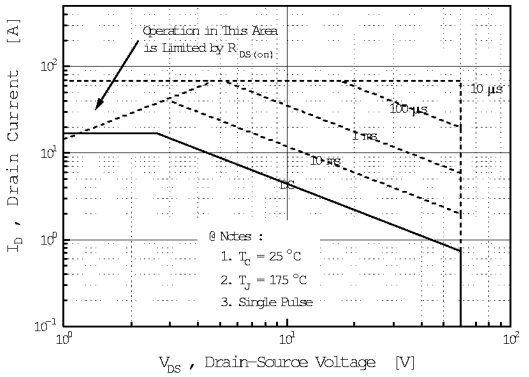


Fig 10. Max. Drain Current vs . Case Temperature

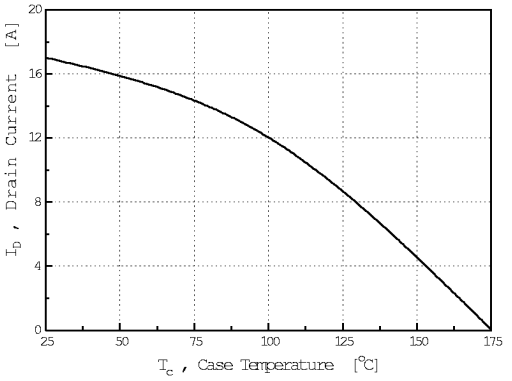


Fig 11. Thermal Response

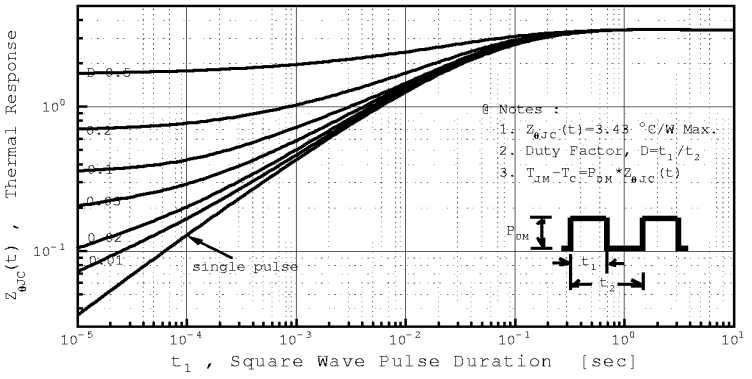


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Fig 12. Gate Charge Test Circuit & Waveform

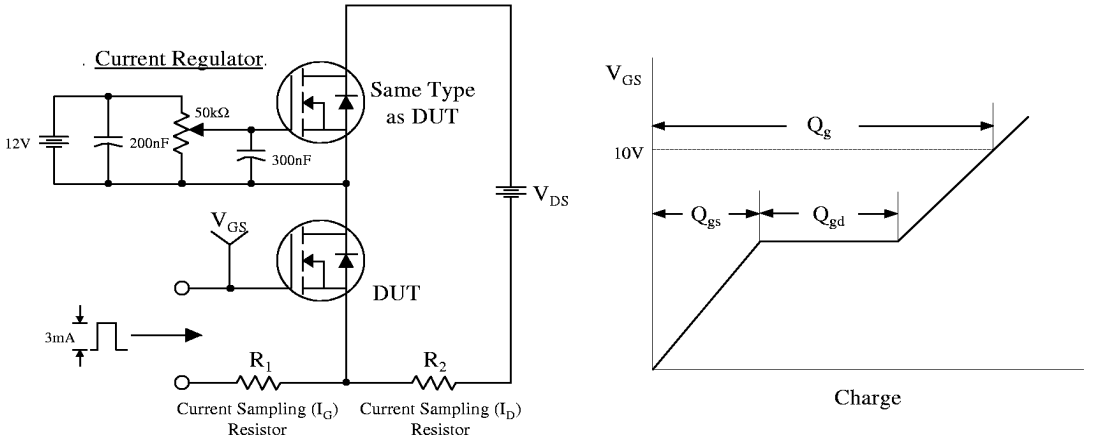

Fig 13. Resistive Switching Test Circuit & Waveforms

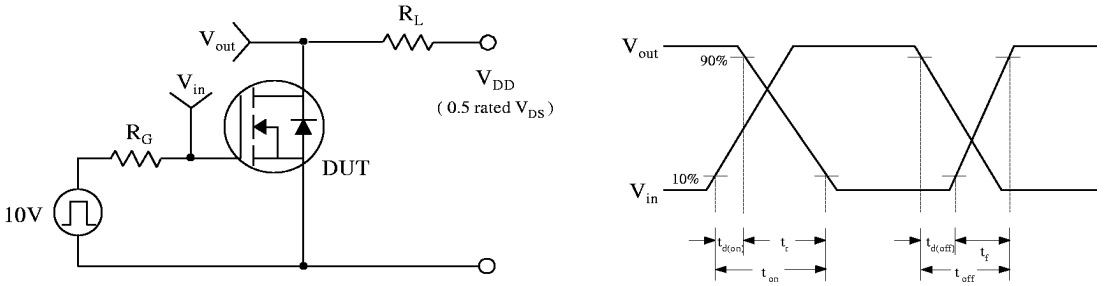

Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

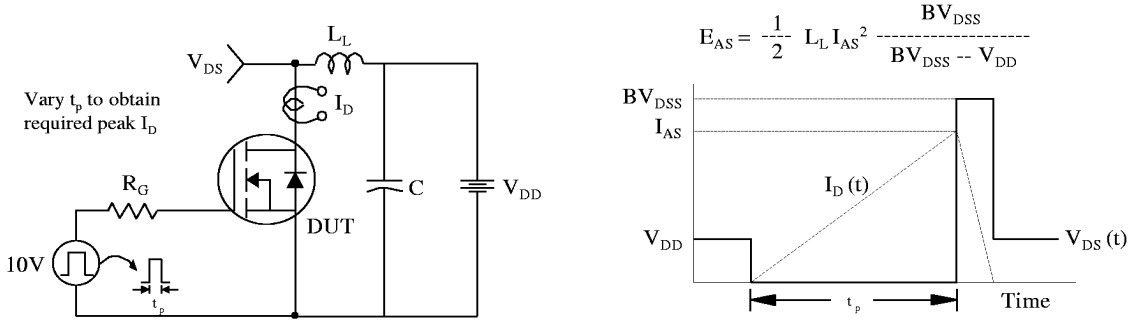

Fig 15. Peak Diode Recovery dv /dt Test Circuit & Waveforms